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#11/C
Amend C
H. K. K. K.
7/24/02

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF:

HIRONOBU KON ET AL

SERIAL NO. 09/684,904

FILED: OCTOBER 10, 2000

FOR: VOLTAGE-DRIVEN POWER
SEMICONDUCTOR DEVICE

:

: GROUP ART UNIT: 2814

:

: EXAMINER: FARAHANI, D.

:

RECEIVED
JUL 23 2002
TECHNOLOGY CENTER 2800

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

In response to the outstanding Office Action mailed April 22, 2002, please amend the
above-identified application as follows:

IN THE CLAIMS

Please amend Claims 23-29 as shown in the attached marked-up copy to read as
follows:

23. (Amended) An injection enhanced gate transistor (IEGT) made of a
semiconductor chip, comprising:
a collector formed on one side of said semiconductor chip;
a gate formed on an opposing side which opposes said one side of the semiconductor
chip;
a main emitter formed on said opposing side of the semiconductor chip; and

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